

MMBT3906LT1G

General Purpose Transistor

PNP Silicon

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	-40	Vdc
Collector – Base Voltage	V_{CBO}	-40	Vdc
Emitter – Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current – Continuous	I_C	-200	mAdc
Collector Current – Peak (Note 3)	I_{CM}	-800	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

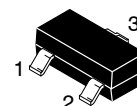
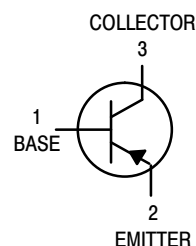
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
- Reference SOA curve.



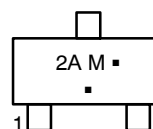
ON Semiconductor®

<http://onsemi.com>



SOT-23 (TO-236)
CASE 318
STYLE 6

MARKING DIAGRAM



2A = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT3906LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT3906LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (I _C = -1.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	-40	–	V _{dc}
Collector – Base Breakdown Voltage (I _C = -10 μA _{dc} , I _E = 0)	V _{(BR)CBO}	-40	–	V _{dc}
Emitter – Base Breakdown Voltage (I _E = -10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	-5.0	–	V _{dc}
Base Cutoff Current (V _{CE} = -30 V _{dc} , V _{EB} = -3.0 V _{dc})	I _{BL}	–	-50	nA _{dc}
Collector Cutoff Current (V _{CE} = -30 V _{dc} , V _{EB} = -3.0 V _{dc})	I _{CEX}	–	-50	nA _{dc}

ON CHARACTERISTICS (Note 4)

DC Current Gain (I _C = -0.1 mA _{dc} , V _{CE} = -1.0 V _{dc}) (I _C = -1.0 mA _{dc} , V _{CE} = -1.0 V _{dc}) (I _C = -10 mA _{dc} , V _{CE} = -1.0 V _{dc}) (I _C = -50 mA _{dc} , V _{CE} = -1.0 V _{dc}) (I _C = -100 mA _{dc} , V _{CE} = -1.0 V _{dc})	H _{FE}	60 80 100 60 30	– – 300 – –	–
Collector – Emitter Saturation Voltage (I _C = -10 mA _{dc} , I _B = -1.0 mA _{dc}) (I _C = -50 mA _{dc} , I _B = -5.0 mA _{dc})	V _{CE(sat)}	– –	-0.25 -0.4	V _{dc}
Base – Emitter Saturation Voltage (I _C = -10 mA _{dc} , I _B = -1.0 mA _{dc}) (I _C = -50 mA _{dc} , I _B = -5.0 mA _{dc})	V _{BE(sat)}	-0.65 –	-0.85 -0.95	V _{dc}

SMALL-SIGNAL CHARACTERISTICS

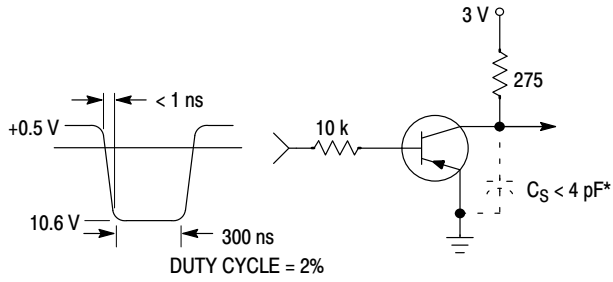
Current – Gain – Bandwidth Product (I _C = -10 mA _{dc} , V _{CE} = -20 V _{dc} , f = 100 MHz)	f _T	250	–	MHz
Output Capacitance (V _{CB} = -5.0 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{obo}	–	4.5	pF
Input Capacitance (V _{EB} = -0.5 V _{dc} , I _C = 0, f = 1.0 MHz)	C _{ibo}	–	10	pF
Input Impedance (I _C = -1.0 mA _{dc} , V _{CE} = -10 V _{dc} , f = 1.0 kHz)	h _{ie}	2.0	12	kΩ
Voltage Feedback Ratio (I _C = -1.0 mA _{dc} , V _{CE} = -10 V _{dc} , f = 1.0 kHz)	h _{re}	0.1	10	X 10 ⁻⁴
Small – Signal Current Gain (I _C = -1.0 mA _{dc} , V _{CE} = -10 V _{dc} , f = 1.0 kHz)	h _{fe}	100	400	–
Output Admittance (I _C = -1.0 mA _{dc} , V _{CE} = -10 V _{dc} , f = 1.0 kHz)	h _{oe}	3.0	60	μmhos
Noise Figure (I _C = -100 μA _{dc} , V _{CE} = -5.0 V _{dc} , R _S = 1.0 kΩ, f = 1.0 kHz)	NF	–	4.0	dB

SWITCHING CHARACTERISTICS

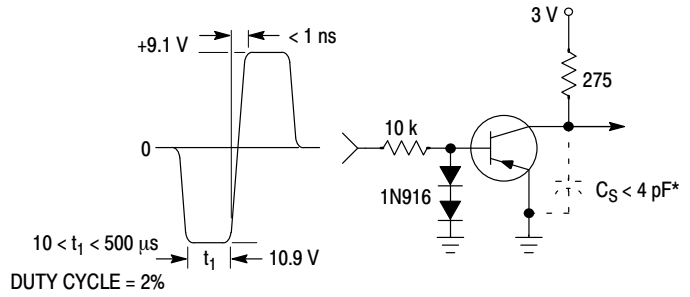
Delay Time	(V _{CC} = -3.0 V _{dc} , V _{BE} = 0.5 V _{dc} , I _C = -10 mA _{dc} , I _{B1} = -1.0 mA _{dc})	t _d	–	35	ns
Rise Time		t _r	–	35	
Storage Time	(V _{CC} = -3.0 V _{dc} , I _C = -10 mA _{dc} , I _{B1} = I _{B2} = -1.0 mA _{dc})	t _s	–	225	ns
Fall Time		t _f	–	75	

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

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**Figure 1. Delay and Rise Time
Equivalent Test Circuit**



**Figure 2. Storage and Fall Time
Equivalent Test Circuit**

* Total shunt capacitance of test jig and connectors

TYPICAL TRANSIENT CHARACTERISTICS

— $T_J = 25^\circ\text{C}$
 - - - $T_J = 125^\circ\text{C}$

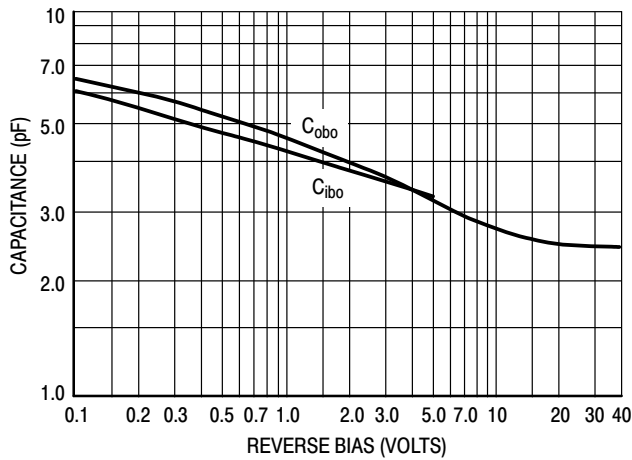


Figure 3. Capacitance

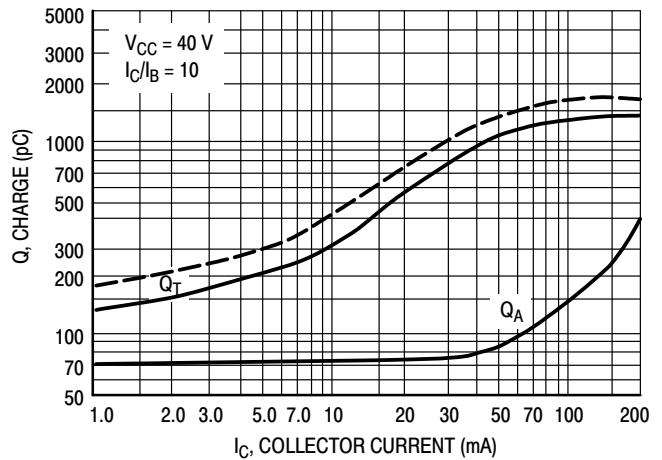


Figure 4. Charge Data

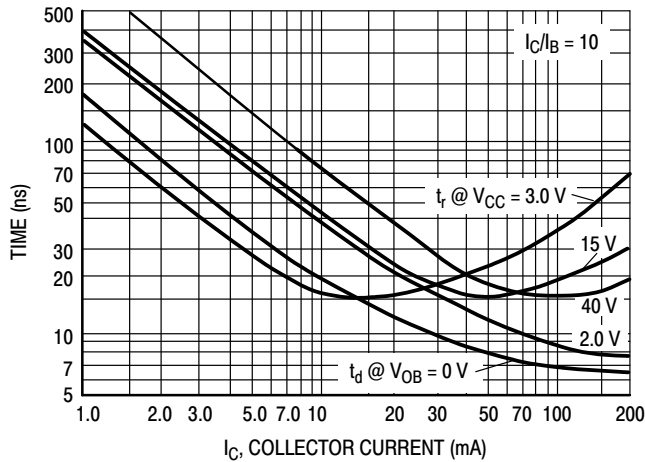


Figure 5. Turn-On Time

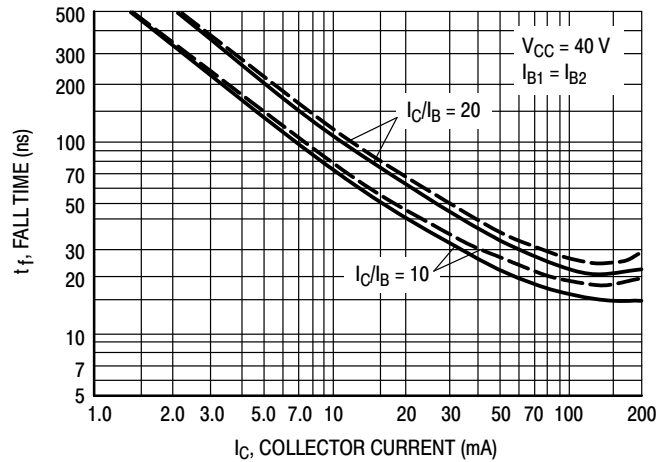


Figure 6. Fall Time

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TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

($V_{CE} = -5.0$ Vdc, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

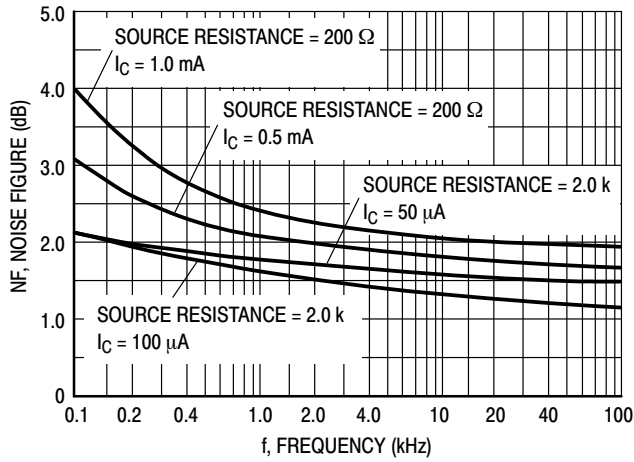


Figure 7.

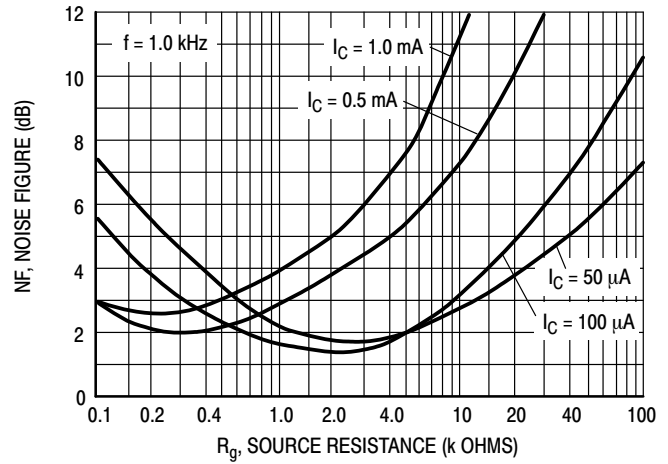


Figure 8.

h PARAMETERS

($V_{CE} = -10$ Vdc, $f = 1.0$ kHz, $T_A = 25^\circ\text{C}$)

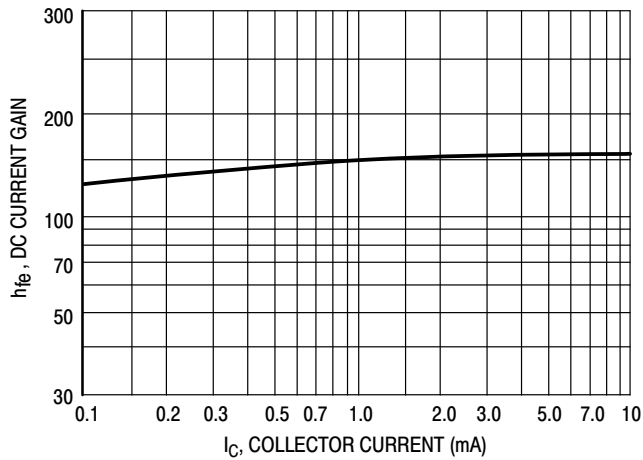


Figure 9. Current Gain

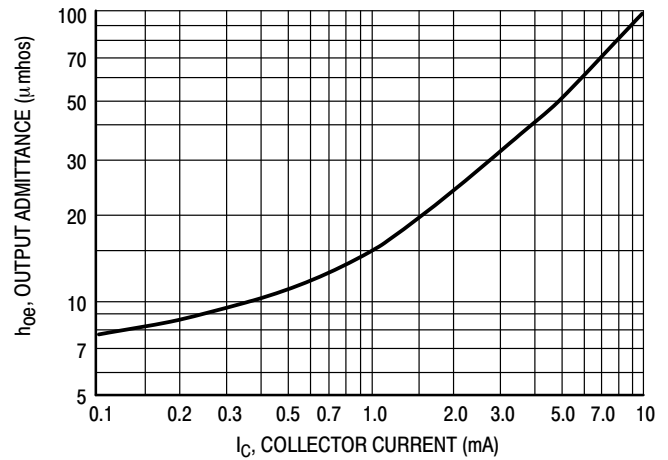


Figure 10. Output Admittance

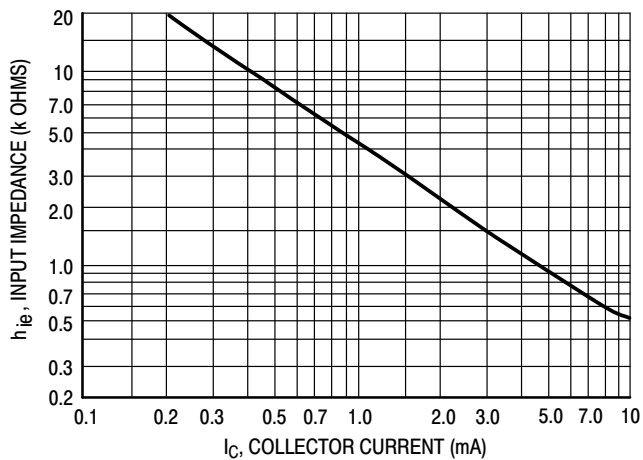


Figure 11. Input Impedance

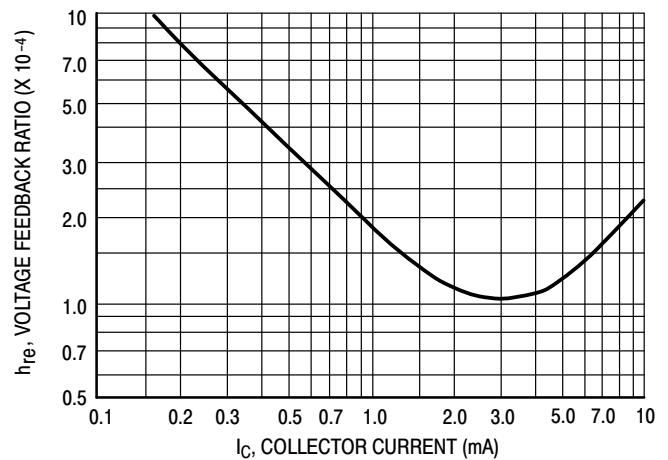


Figure 12. Voltage Feedback Ratio

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TYPICAL STATIC CHARACTERISTICS

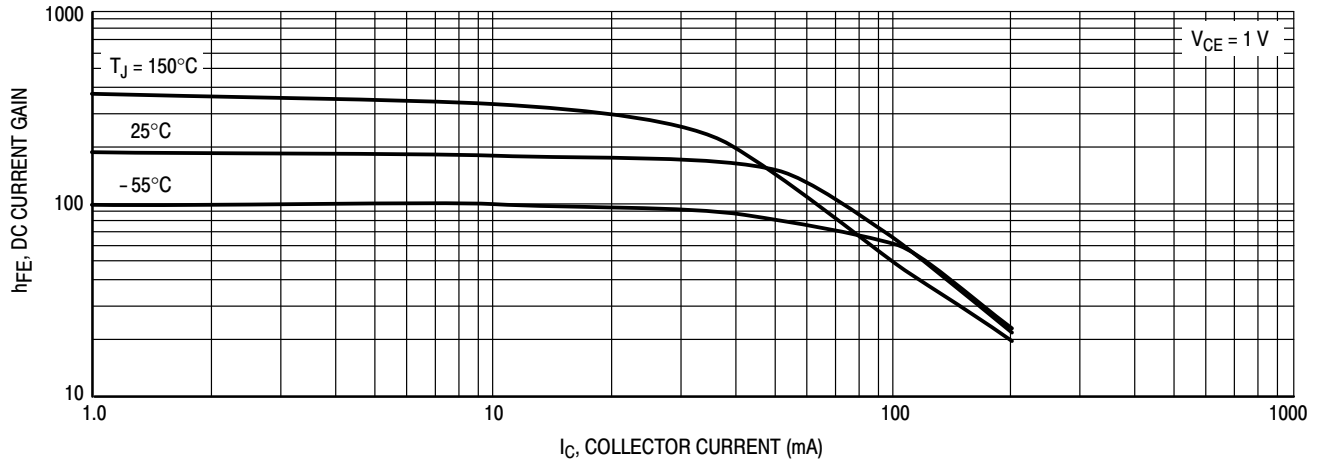


Figure 13. DC Current Gain

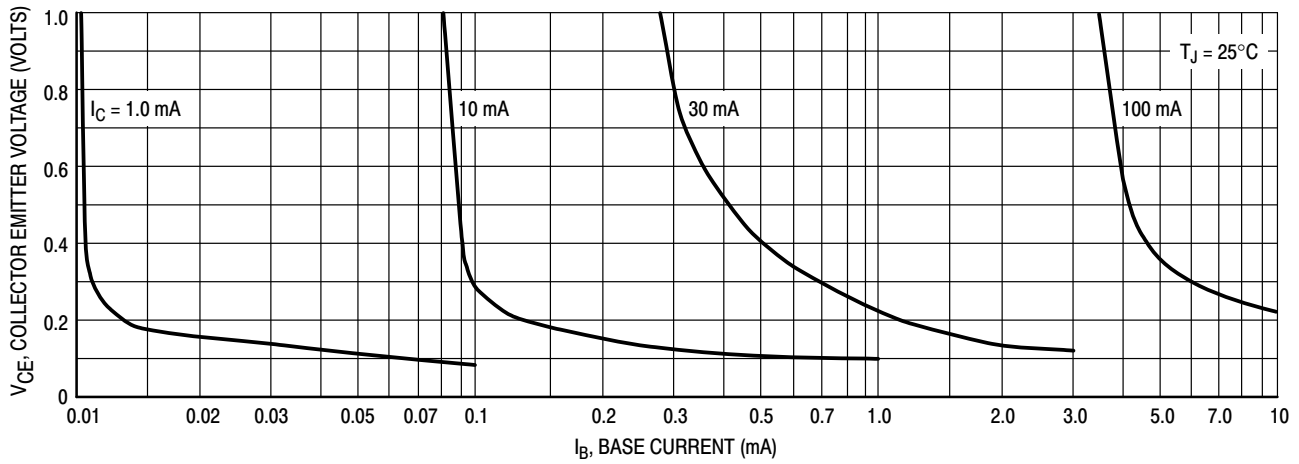


Figure 14. Collector Saturation Region

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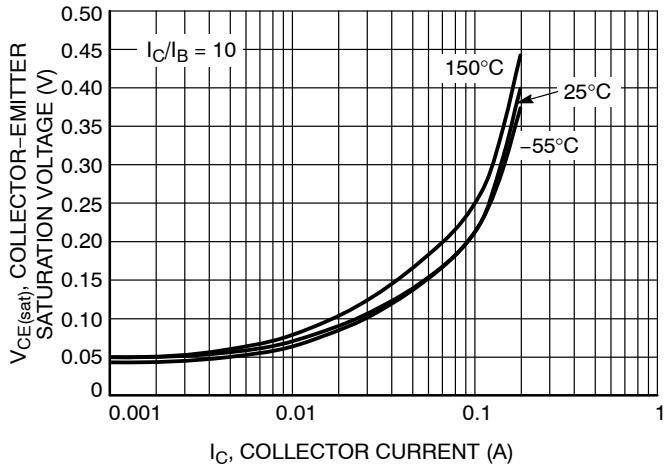


Figure 15. Collector Emitter Saturation Voltage vs. Collector Current

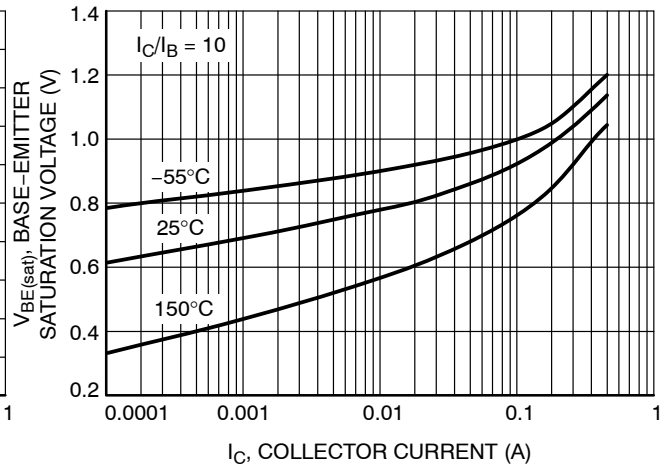


Figure 16. Base Emitter Saturation Voltage vs. Collector Current

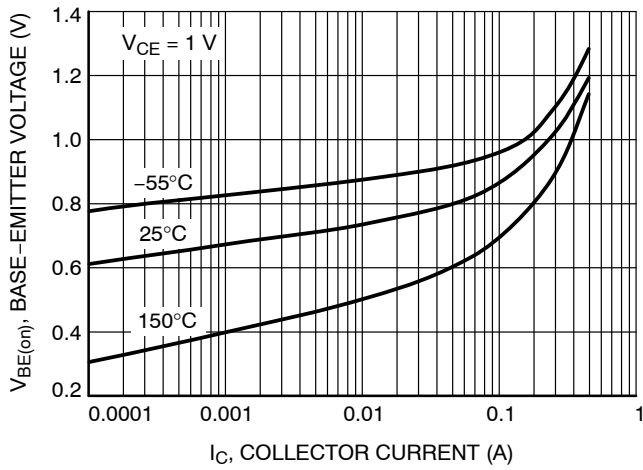


Figure 17. Base Emitter Voltage vs. Collector Current

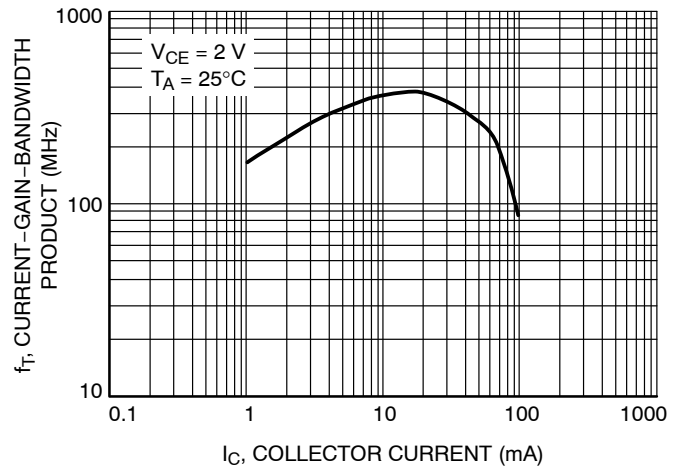


Figure 18. Current Gain Bandwidth vs. Collector Current

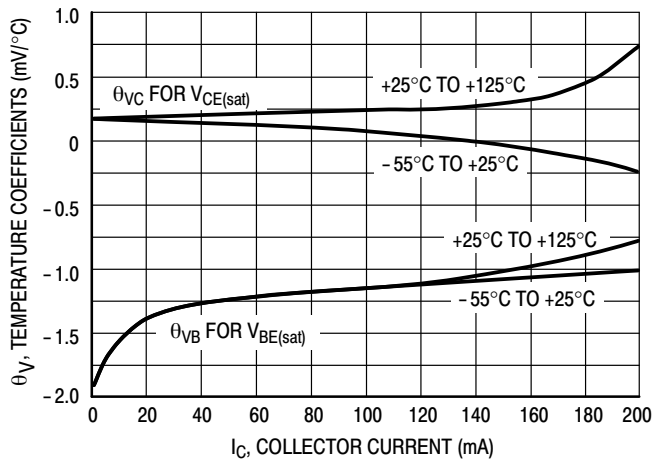


Figure 19. Temperature Coefficients

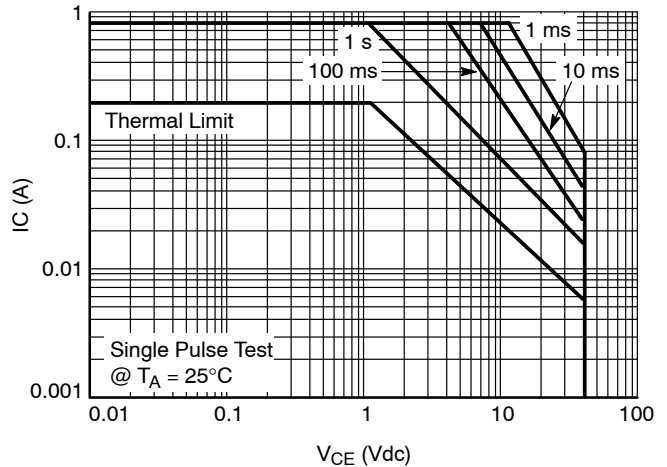
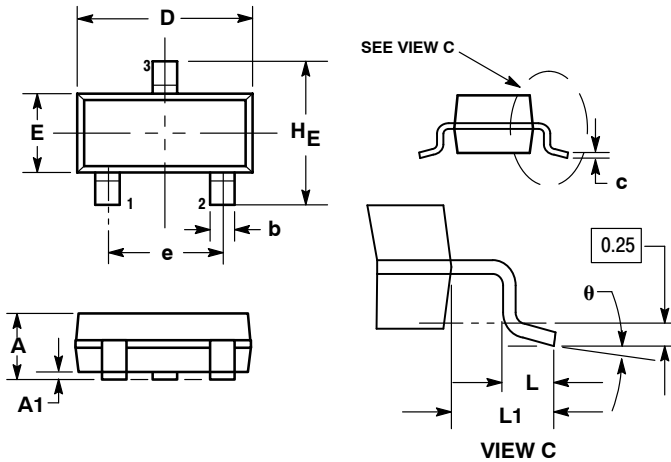


Figure 20. Safe Operating Area

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PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AP



NOTES:

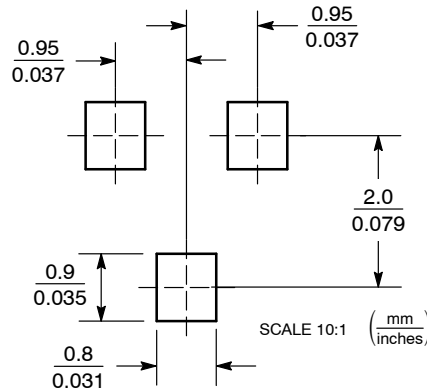
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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